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Back to [PALM](#) | [ASSIGNMENT](#) | [OASIS](#) | [Home page](#)

US 20050264313 A1	US- PGPUB	20051201	Contact probe, measuring pad used for the contact probe, and method of manufacturing the contact probe	324/762		Aoyagi, Masahiro et al.
US 20050236717 A1	US- PGPUB	20051027	System in-package test inspection apparatus and test inspection method	257/775		Aoyagi, Masahiro et al.
US 20050197046 A1	US- PGPUB	20050908	Chemical mechanical polishing method, chemical mechanical polishing system, and manufacturing method of semiconductor device	451/5		Aoyagi, Masahiro et al.
US 20050191763 A1	US- PGPUB	20050901	Superconducting integrated circuit and method for fabrication thereof	438/2	257/E27.007; 257/E39.014; 438/141	Aoyagi, Masahiro et al.
US 20050118805 A1	US- PGPUB	20050602	Method of fabricating semiconductor integrated circuit device	438/682	257/E21.165; 257/E21.548; 257/E21.634; 257/E21.636	Nishihara, Shinji et al.
US 20040256727 A1	US- PGPUB	20041223	Multi-layer fine wiring interposer and manufacturing method thereof	257/758	257/622; 257/E23.067; 257/E25.012; 257/E25.013; 438/118	Aoyagi, Masahiro et al.
US 20040235289 A1	US- PGPUB	20041125	Semiconductor integrated circuit device and method for making the same	438/627	257/E21.295; 257/E21.508; 257/E21.583; 257/E21.584	Suzuki, Masayuki et al.
US 20040203321 A1	US- PGPUB	20041014	Manufacturing method of semiconductor device, automatic operation method and automatic operation system of semiconductor manufacturing apparatus, and automatic operation method of CMP apparatus	451/6		Tsuchiyama, Hirofumi et al.
US 20040106250 A1	US- PGPUB	20040603	Method of fabricating semiconductor integrated circuit device	438/230	257/E21.634; 257/E21.636; 257/E23.16; 257/E29.146; 257/E29.156; 438/592	Nishihara, Shinji et al.
US 20040063263 A1	US- PGPUB	20040401	Manufacturing method of semiconductor devices	438/197	257/E21.55; 257/E21.642; 257/E21.703; 257/E27.112	Suzuki, Norio et al.
US 20040056335 A1	US- PGPUB	20040325	Superconducting integrated circuit and method for fabrication thereof	257/661	257/E27.007; 257/E39.014	Aoyagi, Masahiro et al.
US 20030199161 A1	US- PGPUB	20031023	SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND METHOD FOR MAKING THE SAME	438/622	257/E21.295; 257/E21.508; 257/E21.583; 257/E21.584; 438/629; 438/643;	Suzuki, Masayuki et al.

					438/644; 438/648; 438/653; 438/654; 438/720	
US 20030170980 A1	US- PGPUB	20030911	Semiconductor device and method of manufacturing the same	438/652	257/E23.16; 438/688	Moriya, Hiroshi et al.
US 20030160267 A1	US- PGPUB	20030828	Semiconductor device having a capacitor and a metal interconnect layer with tungsten as a main constituent material and containing molybdenum	257/200	257/E23.163	Iwasaki, Tomio et al.
US 20030020167 A1	US- PGPUB	20030130	Semiconductor device having a capacitor and a metal interconnect layer with tungsten as a main constituent material and containing molybdenum	257/758	257/E23.163	Iwasaki, Tomio et al.
US 20030015801 A1	US- PGPUB	20030123	Semiconductor device	257/758	257/E23.019; 257/E23.163	Nakajima, Takashi et al.
US 20020167091 A1	US- PGPUB	20021114	Semiconductor device having aluminum conductors	257/765	257/750; 257/758; 257/762; 257/E21.295; 257/E21.584; 257/E23.159; 257/E23.16	Iwasaki, Tomio et al.
US 20020137320 A1	US- PGPUB	20020926	PROCESS FOR PRODUCING SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE	438/592	257/E23.16; 257/E29.146; 257/E29.156; 438/221; 438/296	NISHIHARA, SHINJI et al.
US 20020115281 A1	US- PGPUB	20020822	Semiconductor integrated circuit device and method for making the same	438/622	257/E21.295; 257/E21.508; 257/E21.583; 257/E21.584; 438/637; 438/644	Suzuki, Masayuki et al.
US 20020048941 A1	US- PGPUB	20020425	Process for producing semiconductor integrated circuit device	438/669	257/E21.272	Kato, Hisayuki et al.
US 20020036350 A1	US- PGPUB	20020328	Semiconductor device and method of manufacturing the same	257/762	257/E23.16	Moriya, Hiroshi et al.
US 20020024140 A1	US- PGPUB	20020228	Semiconductor device	257/758	257/E23.019; 257/E23.163	Nakajima, Takashi et al.
US 20020019124 A1	US- PGPUB	20020214	Semiconductor integrated circuit device and method for making the same	438/623	257/E21.295; 257/E21.508; 257/E21.583; 257/E21.584; 438/625;	Suzuki, Masayuki et al.

					438/678	
US 20010042920 A1	US- PGPUB	20011122	Semiconductor device	257/758	257/E23.163	Iwasaki, Tomio et al.
US 20010023958 A1	US- PGPUB	20010927	Semiconductor integrated circuit device for connecting semiconductor region and electrical wiring metal via titanium silicide layer and method of fabrication thereof	257/307	257/E23.019; 257/E23.145; 438/399	Todorobaru, Hiromi et al.
US 6911665 B2	USPAT	20050628	Superconducting integrated circuit and method for fabrication thereof	257/32	257/31; 257/33; 257/E27.007; 257/E39.014; 505/191; 505/233	Aoyagi, Masahiro et al.
US 6858484 B2	USPAT	20050222	Method of fabricating semiconductor integrated circuit device	438/199	257/351; 257/369; 257/E21.634; 257/E21.636; 257/E23.16; 257/E29.146; 257/E29.156; 438/153; 438/154; 438/651; 438/682	Nishihara, Shinji et al.
US 6856021 B1	USPAT	20050215	Semiconductor device having aluminum alloy conductors	257/766	257/758; 257/E21.295; 257/E21.584; 257/E23.159; 257/E23.16	Iwasaki, Tomio et al.
US 6784549 B2	USPAT	20040831	Semiconductor device having a capacitor and a metal interconnect layer with tungsten as a main constituent material and containing molybdenum	257/758	257/295; 257/E23.163	Iwasaki, Tomio et al.
US 6780757 B2	USPAT	20040824	Semiconductor integrated circuit device and method for making the same	438/623	257/E21.295; 257/E21.508; 257/E21.583; 257/E21.584; 438/672	Suzuki, Masayuki et al.
US 6693001 B2	USPAT	20040217	Process for producing semiconductor integrated circuit device	438/199	257/351; 257/369; 257/E23.16; 257/E29.146; 257/E29.156; 438/153; 438/154; 438/651; 438/682	Nishihara, Shinji et al.
US 6656828 B1	USPAT	20031202	Method of forming bump electrodes	438/613	257/E21.508; 257/E21.584; 438/614	Maitani, Touta et al.

US 6617691 B2	USPAT	20030909	Semiconductor device	257/758	257/296; 257/314; 257/66; 257/780; 257/781; 257/785; 257/E23.019; 257/E23.163	Nakajima; Takashi et al.
US 6583049 B2	USPAT	20030624	Semiconductor integrated circuit device and method for making the same	438/623	257/E21.295; 257/E21.508; 257/E21.583; 257/E21.584; 438/672	Suzuki; Masayuki et al.
US 6548904 B2	USPAT	20030415	Semiconductor device having a capacitor and a metal interconnect layer with tungsten as a main constituent material and containing molybdenum	257/758	257/295; 257/E23.163; 438/618; 438/622; 438/624	Iwasaki; Tomio et al.
US 6545362 B2	USPAT	20030408	Semiconductor device and method of manufacturing the same	257/765	257/750; 257/751; 257/762; 257/771; 257/E23.16; 438/652; 438/653; 438/672; 438/688	Moriya; Hiroshi et al.
US 6538329 B2	USPAT	20030325	Semiconductor integrated circuit device and method for making the same	257/765	257/E21.295; 257/E21.508; 257/E21.583; 257/E21.584	Suzuki; Masayuki et al.
US 6503803 B2	USPAT	20030107	Method of fabricating a semiconductor integrated circuit device for connecting semiconductor region and electrical wiring metal via titanium silicide layer	438/296	257/E23.019; 257/E23.145; 438/637; 438/638; 438/639	Todorobaru; Hiromi et al.
US 6476492 B2	USPAT	20021105	Semiconductor device having a capacitor and an interconnect layer with molybdenum-containing tungsten	257/758	257/295; 257/E23.163; 438/618; 438/622; 438/624	Iwasaki; Tomio et al.
US 6472754 B2	USPAT	20021029	Semiconductor device with improved arrangements to avoid breakage of tungsten interconnector	257/758	257/296; 257/57; 257/59; 257/66; 257/E23.019; 257/E23.163	Nakajima; Takashi et al.
US 6326216 B1	USPAT	20011204	Process for producing semiconductor integrated circuit device	438/3	257/295; 257/E21.272; 438/240	Kato; Hisayuki et al.
US 6300237 B1	USPAT	20011009	Semiconductor integrated circuit device and method for making the same	438/623	257/E21.295; 257/E21.508; 257/E21.583;	Suzuki; Masayuki et al.

					257/E21.584; 438/672	
US 6268658 B1	USPAT	20010731	Semiconductor integrated circuit device for connecting semiconductor region and electrical wiring metal via titanium silicide layer and method of fabrication thereof	257/763	257/764; 257/767; 257/E23.019; 257/E23.145	Todorobaru; Hiromi et al.
US 6031288 A	USPAT	20000229	Semiconductor integrated circuit device for connecting semiconductor region and electrical wiring metal via titanium silicide layer and method of fabrication thereof	257/754	257/755; 257/763; 257/768; 257/770; 257/E23.019; 257/E23.145	Todorobaru; Hiromi et al.
US 5904556 A	USPAT	19990518	Method for making semiconductor integrated circuit device having interconnection structure using tungsten film	438/623	257/E21.295; 257/E21.508; 257/E21.583; 257/E21.584; 438/625; 438/672	Suzuki; Masayuki et al.
US 5598105 A	USPAT	19970128	Elementary cell for constructing asynchronous superconducting logic circuits	326/6	326/1; 326/3	Kurosawa; Itaru et al.
US 5444012 A	USPAT	19950822	Method for manufacturing semiconductor integrated circuit device having a fuse element	438/6	148/DIG.55; 257/E21.661; 257/E23.149; 438/281; 438/601	Yoshizumi; Keiichi et al.
US 5260264 A	USPAT	19931109	Josephson memory circuit	505/170	257/31; 257/33; 257/36; 365/162; 505/191; 505/702; 505/832; 505/874	Kurosawa; Itaru et al.
US 5188975 A	USPAT	19930223	Method of producing a connection hole for a DRAM having at least three conductor layers in a self alignment manner.	438/396	257/E21.252; 257/E21.274; 257/E21.575; 257/E21.577; 438/632; 438/637	Kojima; Masayuki et al